

isc Silicon PNP Power Transistor

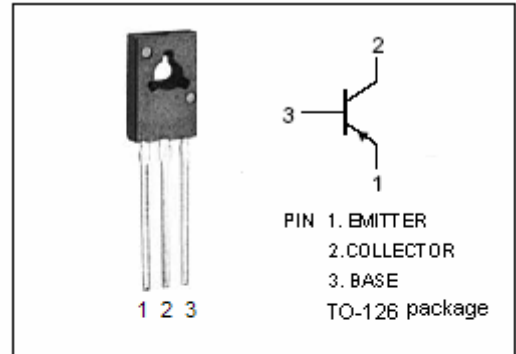
MJE371

DESCRIPTION

- Collector–Emitter Sustaining Voltage—
: $V_{CEO(SUS)} = -40V$
- DC Current Gain—
: $h_{FE} = 40(\text{Min}) @ I_C = -1A$
- Complement to Type MJE521

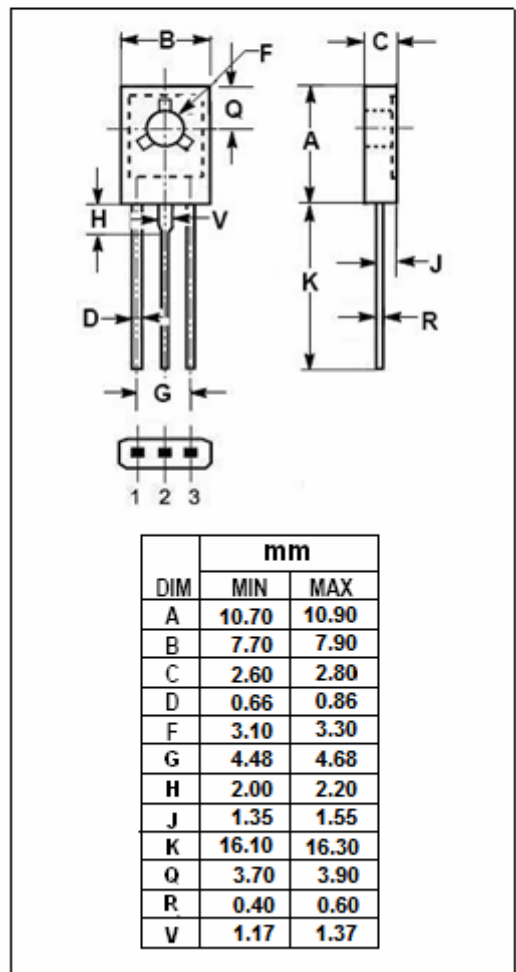
APPLICATIONS

- Designed for use in general-purpose amplifier and switching circuits.
- Recommended for use in 5~20 Watt audio amplifiers utilizing complementary symmetry circuitry.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-peak	-8	A
I_B	Base Current	-2	A
P_C	Collector Power Dissipation $T_C=25^\circ C$	40	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.12	$^\circ C/W$

isc Silicon PNP Power Transistor**MJE371****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -100\text{mA}; I_B = 0$	-40		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -40\text{V}; I_E = 0$		-100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$		-100	μA
h_{FE}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -1\text{V}$	40		